

**TGD N-Channel Super Trench Power MOSFET**

**Description**

The TGDP01T11 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

**General Features**

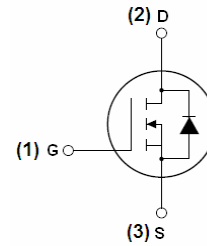
- $V_{DS} = 100V, I_D = 108A$   
 $R_{DS(ON)} < 6.5m\Omega @ V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

**Application**

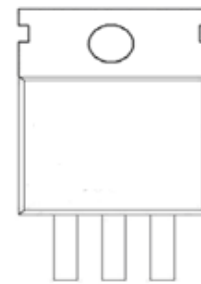
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

**100% UIS TESTED!**

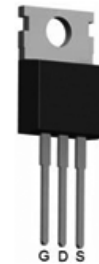
**100% ΔVds TESTED!**



Schematic diagram



pin assignment



TO-220-3L top view

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
TGDP01T11	TGDP01T11	TO-220-3L	-	-	-

**Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	108	A
Drain Current-Continuous(T <sub>C</sub> =100°C)	$I_D (100^\circ C)$	78	A
Pulsed Drain Current	$I_{DM}$	380	A
Maximum Power Dissipation	$P_D$	160	W
Derating factor		1.1	W/°C
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	676	mJ



Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C
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**Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	0.94	°C/W
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**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	-	4.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=50A$	-	5.7	6.5	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=50A$	40	-	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	5200	-	PF
Output Capacitance	$C_{oss}$		-	790	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	47	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=50A$ $V_{GS}=10V, R_G=4.7\Omega$	-	13.8	-	nS
Turn-on Rise Time	$t_r$		-	13	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	39	-	nS
Turn-Off Fall Time	$t_f$		-	14	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=50A,$ $V_{GS}=10V$	-	60		nC
Gate-Source Charge	$Q_{gs}$		-	21		nC
Gate-Drain Charge	$Q_{gd}$		-	11		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=108A$	-		1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	108	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}, I_F = I_S$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-	74		nS
Reverse Recovery Charge	$Q_{rr}$		-	176		nC

**Notes:**

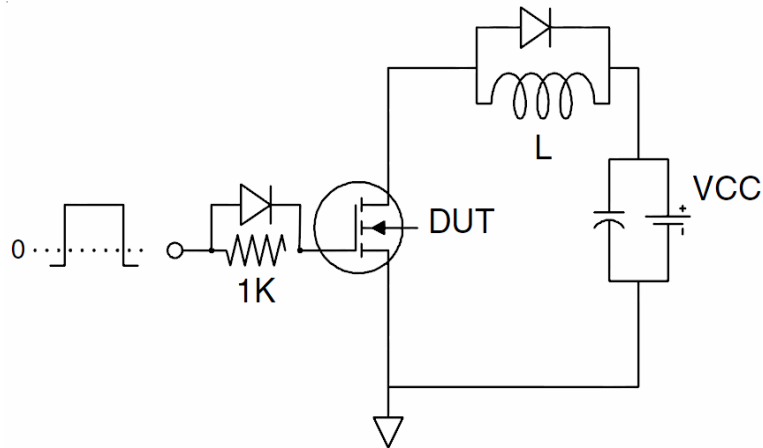
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Test Circuit

1)  $E_{AS}$  test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

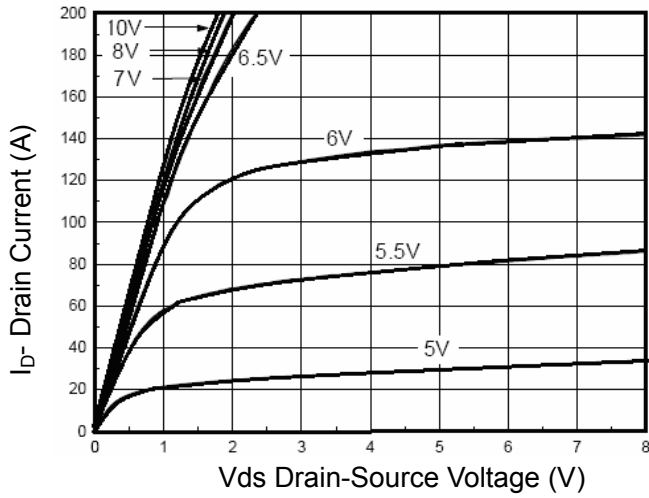


Figure 1 Output Characteristics

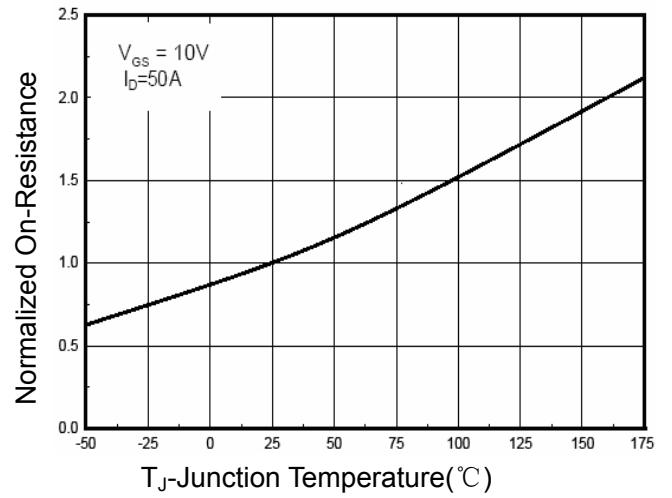


Figure 4 Rdson-Junction Temperature

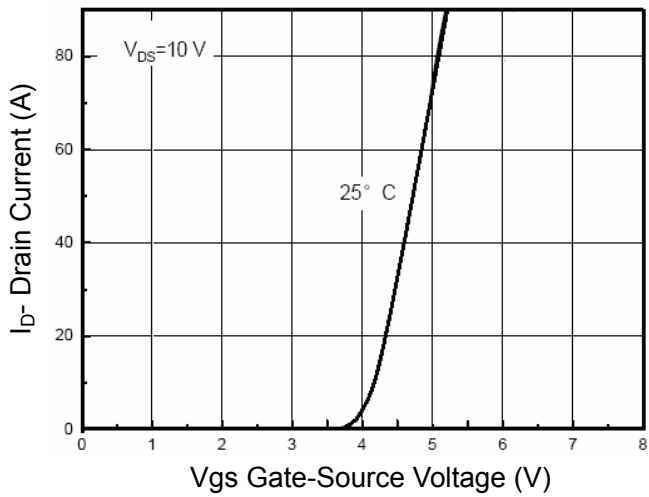


Figure 2 Transfer Characteristics

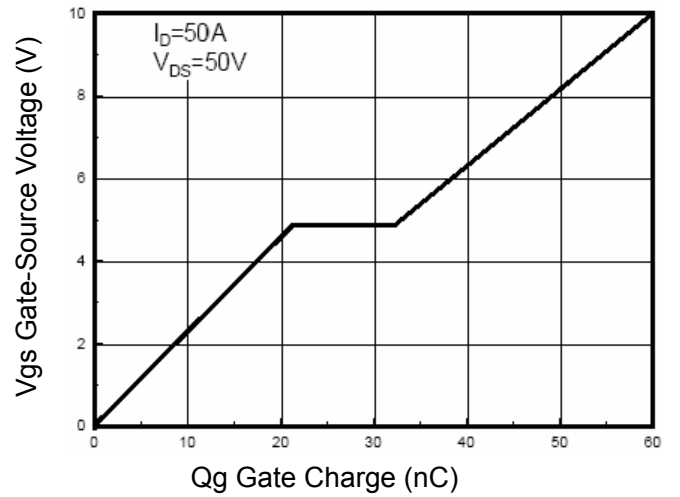


Figure 5 Gate Charge

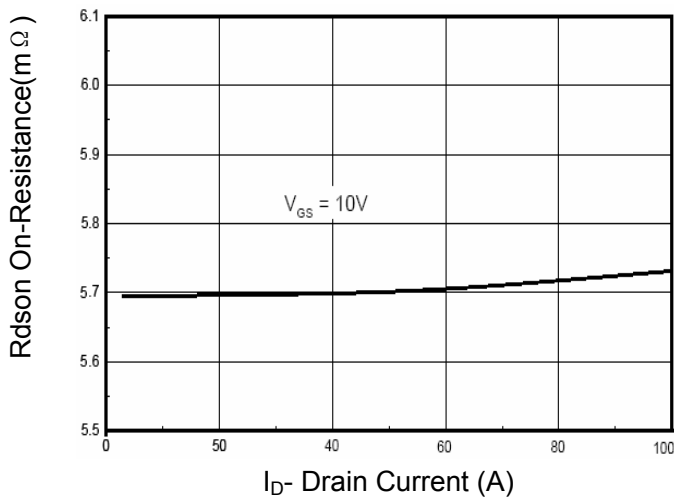


Figure 3 Rdson- Drain Current

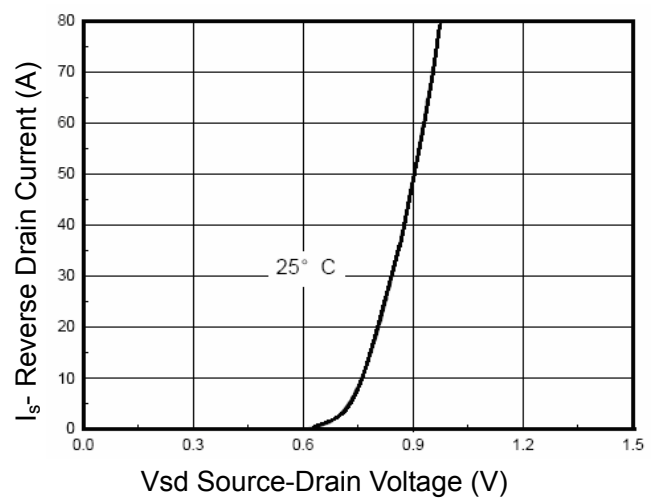


Figure 6 Source- Drain Diode Forward

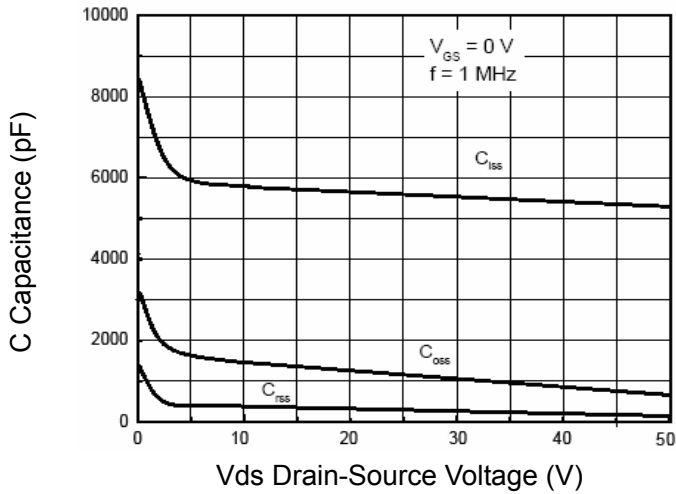


Figure 7 Capacitance vs Vds

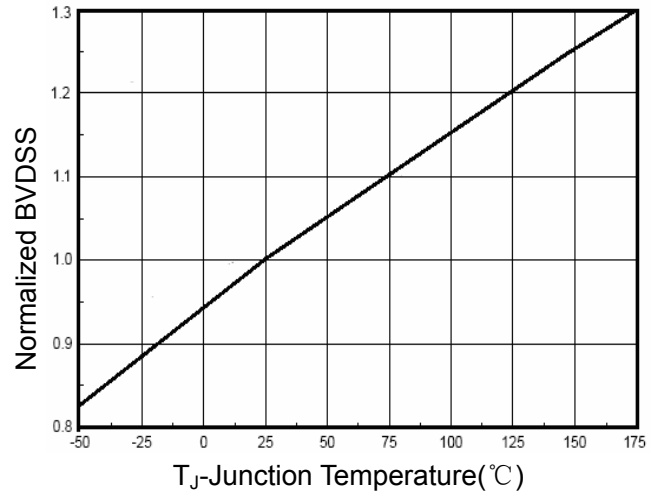


Figure 9  $BV_{DSS}$  vs Junction Temperature

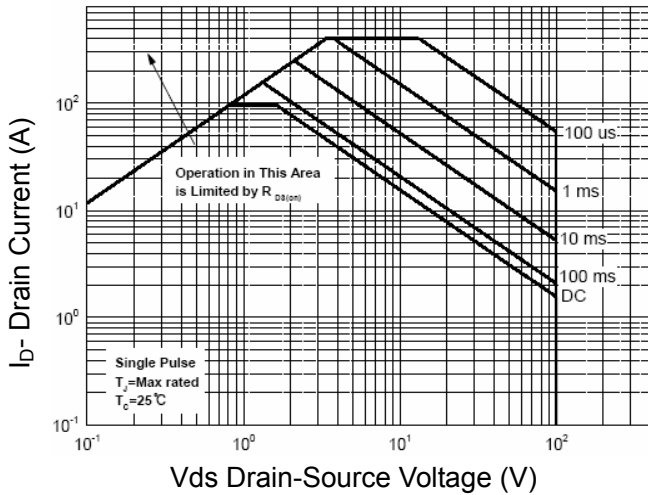


Figure 8 Safe Operation Area

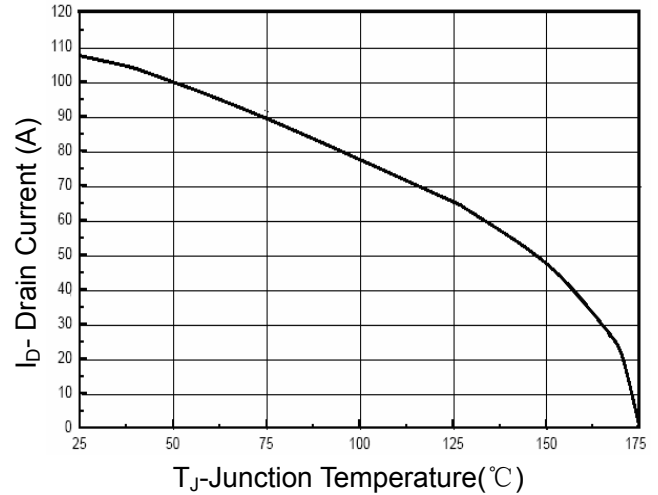


Figure 10 Current De-rating

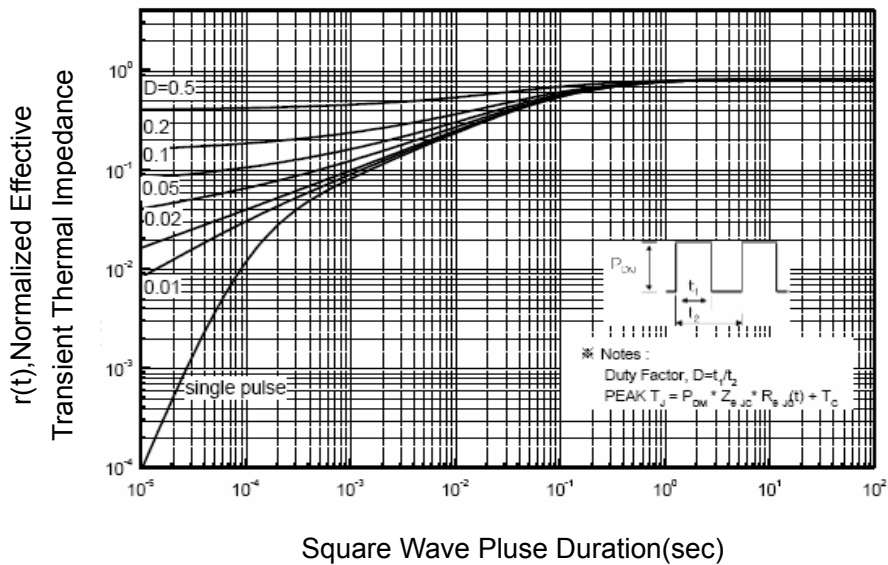
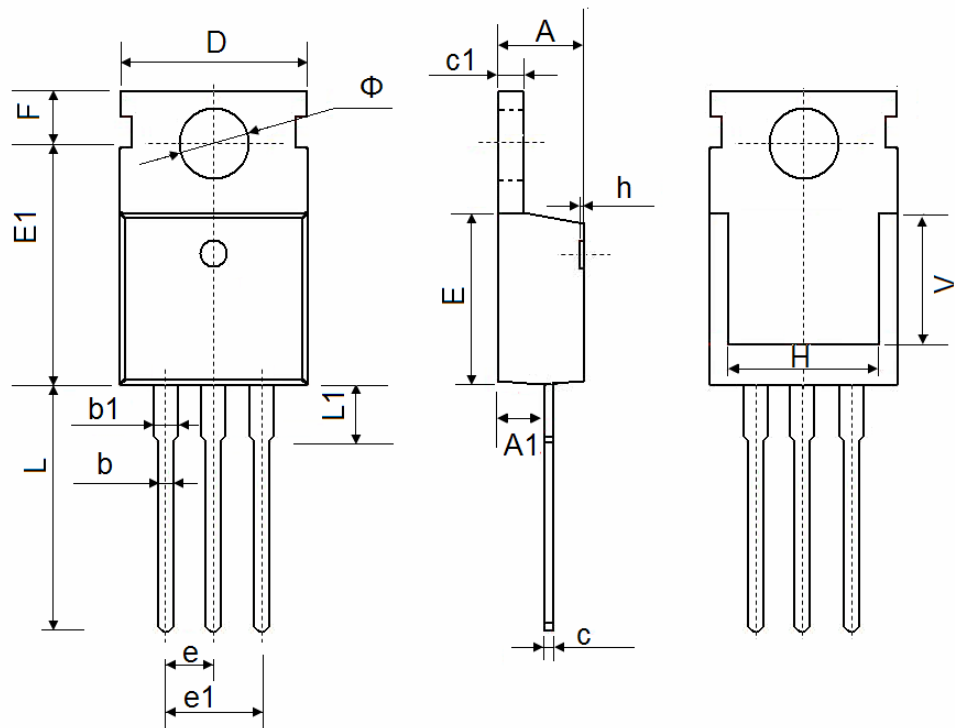


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150